

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	118337 67	Si near3 Ge near "3" C	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	214020	boron or phosphorous	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	16854	(B or Ph) with (doping or dopant or dope or doped)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	0	silcon with (carbon or carbide) with germanium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	117	silcon with (carbon or carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	0	5 with germanium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L7	1	5 same germanium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	52055	1 same 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	7459	1 same 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	0	7 same (2 or 3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	L11	58562	8 or 9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	L12	410633	resistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	L13	174980 5	resistance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	L14	94612	resistivity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	L15	1873	11 and 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	L16	4594	11 same (12 or 13 or 14)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	24487	338/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L18	104	16 and 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	BRS	L19	1817	Si near3 Ge near3 C	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	L20	58562	1 same (2 or 3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	BRS	L21	109	19 same (2 or 3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	97193	SiC or (silicon ADJ carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	12	SiCGe	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	1971	1 with (Ge or Germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	240	3 same (doped or dopant or doping or dope)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	34	4 same (resistor or resistance or resistivity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	1468	Si NEar2 Ge near2 C	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	295854	boron or phosphorus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	420	1 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	414166	resistor sane 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	5	resistor same 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L7	0	2 and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L6	5	4 and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L8	199879 5	resistor or resitivity or resistance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	L9	79	8 same 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	16	2 and 9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	L11	1253	silicon near2 germanium near2 carbon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	L12	54	11 same 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	L13	35	2 and 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	L14	33	13 not 10	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	L15	16832	(B or Ph) WITH (doping or doped or dope or dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	L16	2574	11 or 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	L #	Hits	Search Text	DBs
17	BRS	L17	126	16 same 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L18	1	17 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB